

## Description

Product Summary		
V <sub>DS</sub> (V)	R <sub>DS(on)</sub> (mΩ)(Typ)	I <sub>D</sub> (A)
650	70@ V <sub>GS</sub> = 12V	27

## Feature

- Easy to use, compatible with standard gate drivers
- Excellent Q<sub>G</sub> x R<sub>DS(on)</sub> figure of merit (FOM)
- Low Q<sub>RR</sub>, no free-wheeling diode required
- Low switching loss
- RoHS compliant and Halogen-free

## Applications

- High efficiency power supplies
- Telecom and datacom
- Automotive
- Servo motors

## Absolute maximum rating@25°C

Parameter	Symbol	Rating	Unit
Drain-Source Voltage	V <sub>DS</sub>	650	V
Gate-Source Voltage	V <sub>GS</sub>	±20	V
Transient Drain-Source Voltage <sup>1)</sup>	V <sub>TDS</sub>	800	V
Continuous Drain Current	T <sub>C</sub> =25°C	I <sub>D</sub>	A
	T <sub>C</sub> =100°C		
Pulsed Drain Current (Pulse Width: 100μs)	T <sub>C</sub> =25°C	I <sub>DM</sub>	A
	T <sub>C</sub> =100°C		
Power Dissipation	P <sub>D</sub>	93	W
Soldering Peak Temperature	T <sub>CSOLD</sub>	260	°C
Operating Junction and Storage Temperature	T <sub>J</sub> , T <sub>STG</sub>	-55 to 150	°C

## Thermal Resistance

Parameter	Symbol	Min	Typ	Max	Unit
Thermal Resistance, Junction-to-Case	R <sub>θJC</sub>	-	1.34	-	°C/W
Thermal Resistance, Junction-to-Ambient <sup>2)</sup>	R <sub>θJA</sub>	-	50	-	°C/W

# 650V GaN Power Transistor

PGCTO65R70A

## Electrical characteristics per line@25°C (unless otherwise specified)

Parameter	Symbol	Conditions		Min.	Typ.	Max.	Units	
<b>Statistic Characteristics</b>								
Maximum Drain-Source Voltage	V <sub>DS-Max</sub>	V <sub>GS</sub> = 0V		650	-	-	V	
Drain-Source Breakdown Voltage	BV <sub>DSS</sub>	V <sub>GS</sub> = 0V, I <sub>D</sub> = 250μA		-	1000	-	V	
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	V <sub>DS</sub> =650V, V <sub>GS</sub> =0V	T <sub>J</sub> =25°C	-	10	30	μA	
			T <sub>J</sub> =150°C	-	50	-		
Gate-Body Leakage Current	I <sub>GSS</sub>	V <sub>GS</sub> = ±20V, V <sub>DS</sub> = 0V		-	-	±150	nA	
Gate Threshold Voltage	V <sub>GS(th)</sub>	V <sub>DS</sub> = V <sub>GS</sub> , I <sub>D</sub> = 500μA	3.0	4.0	5.0	-	V	
Gate Threshold Voltage Temperature Coefficient	△V <sub>GS(th)</sub> /T <sub>J</sub>			-	-11.3	-	mV/°C	
Drain-Source On-State Resistance <sup>3)</sup>	R <sub>DS(ON)</sub>	V <sub>GS</sub> =12V, I <sub>D</sub> =4A	T <sub>J</sub> =25°C	-	70	90	mΩ	
			T <sub>J</sub> =150°C	-	140	-		
<b>Dynamic Characteristics</b>								
Input Capacitance	C <sub>iss</sub>	V <sub>DS</sub> = 400V, V <sub>GS</sub> = 0V, f = 1MHz	V <sub>GS</sub> = 0V, V <sub>DS</sub> = 0-400V	-	354	-	pF	
Output Capacitance	C <sub>oss</sub>			-	79.7	-		
Reverse Transfer Capacitance	C <sub>rss</sub>			-	1.9	-		
Effective Output Capacitance, Energy Related	C <sub>o(er)</sub>	V <sub>GS</sub> = 0V, V <sub>DS</sub> = 0-400V	V <sub>GS</sub> = 0V, V <sub>DS</sub> = 0-400V	-	120	-	pF	
Effective Output Capacitance, Time Related	C <sub>o(tr)</sub>			-	217	-		
Output Charge	Q <sub>oss</sub>			-	87	-	nC	
Turn-on Delay Time	t <sub>d(on)</sub>	V <sub>DS</sub> = 400V, I <sub>D</sub> = 10A, V <sub>GS</sub> = 0-12V, R <sub>G</sub> = 40Ω	V <sub>GS</sub> = 0V, V <sub>DS</sub> = 0-400V	-	44	-	ns	
Turn-on Rise Time	t <sub>r</sub>			-	16	-		
Turn-Off Delay Time	t <sub>d(off)</sub>			-	40	-		
Turn-Off Fall Time	t <sub>f</sub>			-	12	-		
Total Gate Charge	Q <sub>g</sub>	V <sub>DS</sub> = 400V, I <sub>D</sub> = 6A, V <sub>GS</sub> = 0-12V	V <sub>GS</sub> = 0V, V <sub>DS</sub> = 0-400V	-	17	-	nC	
Gate-Source Charge	Q <sub>gs</sub>			-	4.6	-		
Gate-Drain Charge	Q <sub>gd</sub>			-	5.6	-		
<b>Reverse Diode Characteristics</b>								
Diode Forward Voltage	V <sub>SD</sub>	V <sub>GS</sub> =0V, I <sub>S</sub> =8.5A		-	1.3	-	V	
		V <sub>GS</sub> =0V, I <sub>S</sub> =17A	T <sub>J</sub> =25°C	-	1.9	-		
			T <sub>J</sub> =150°C	-	3.0	-		
Reverse Recovery Time	t <sub>rr</sub>	V <sub>GS</sub> =0V, I <sub>S</sub> =17A, V <sub>DD</sub> =400V, di/dt=1000A/μs		-	33	-	ns	
Reverse Recovery Charge	Q <sub>rr</sub>			-	87	-	μC	

Notes:

1. Off-state spike duty cycle < 0.01, spike duration < 2μs
2. Device on one layer epoxy PCB for drain connection (vertical and without air stream cooling, with 6cm<sup>2</sup>copper area and 70μm thickness)
3. Dynamic on-resistance; see Figure 18 and 19 for test circuit and configurations

## Typical Characteristics

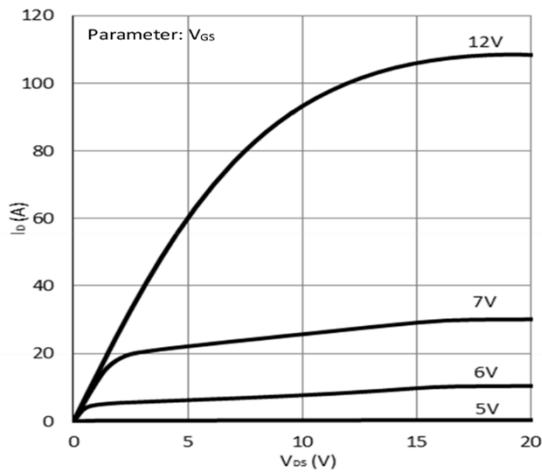
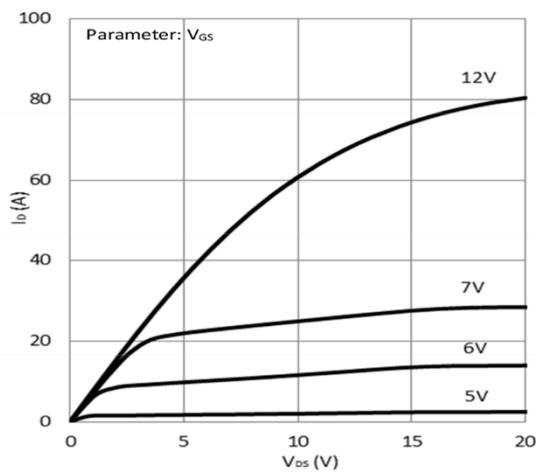
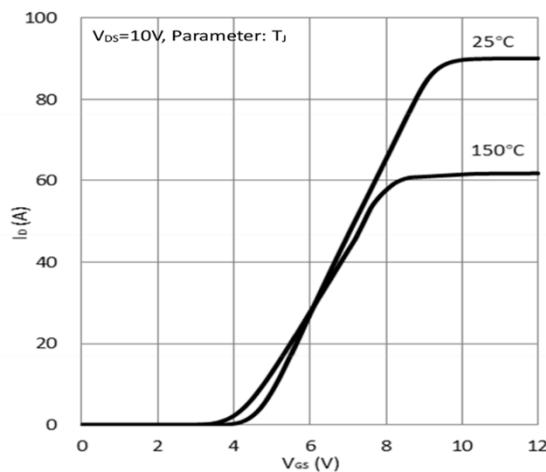
Figure 1. Typical Output Characteristics  $T_j=25^\circ\text{C}$ Figure 2. Typical Output Characteristics  $T_j=150^\circ\text{C}$ 

Figure 3. Typical Transfer Characteristics

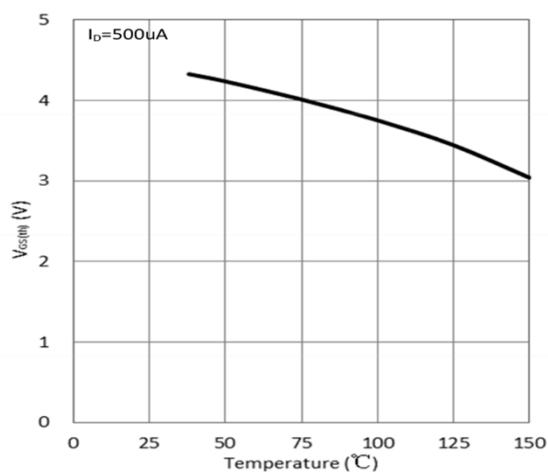
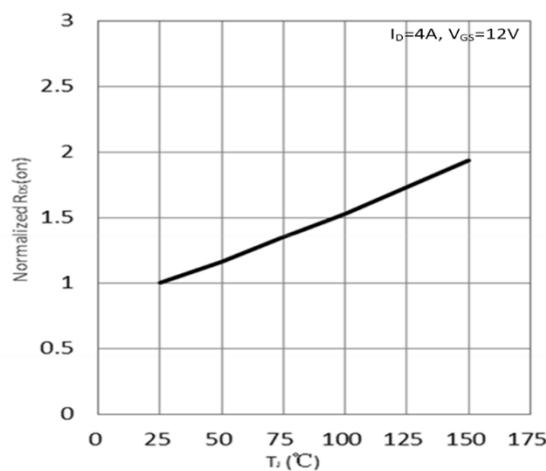
Figure 4.  $V_{GS(\text{th})}$  Vs Temperature Characteristics

Figure 5. Normalized On-resistance

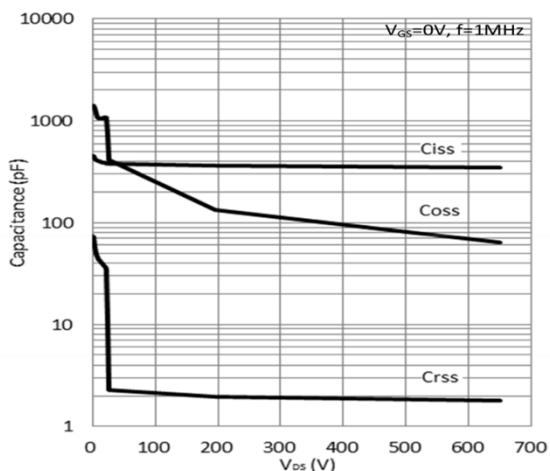


Figure 6. Typical Capacitance

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PGCTO65R70A

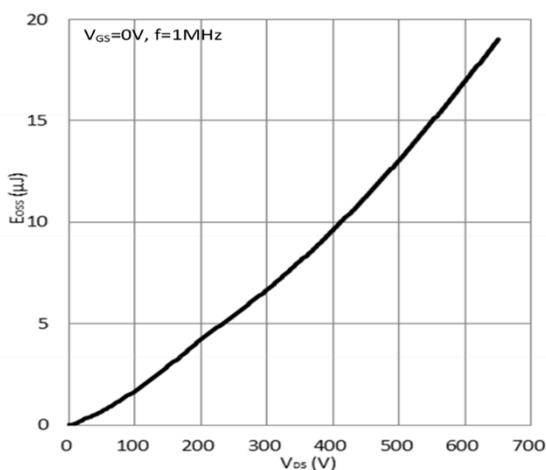


Figure 7. Typical Coss Stored Energy

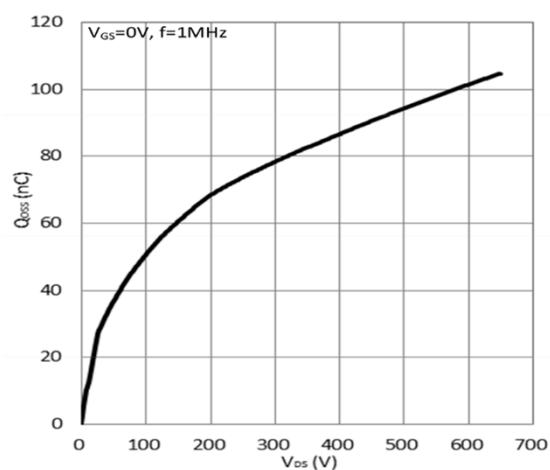


Figure 8. Typical Qoss

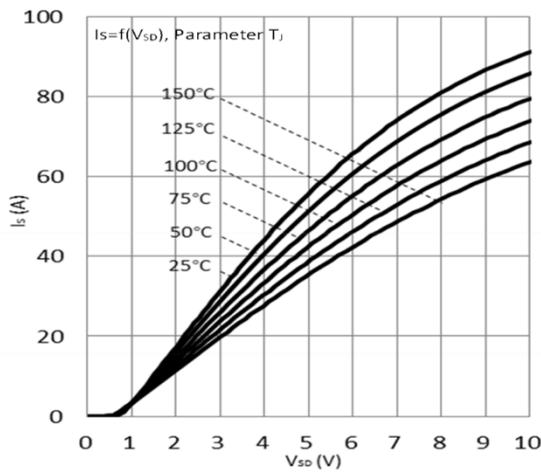


Figure 9. Forward Characteristic of Rev. Diode

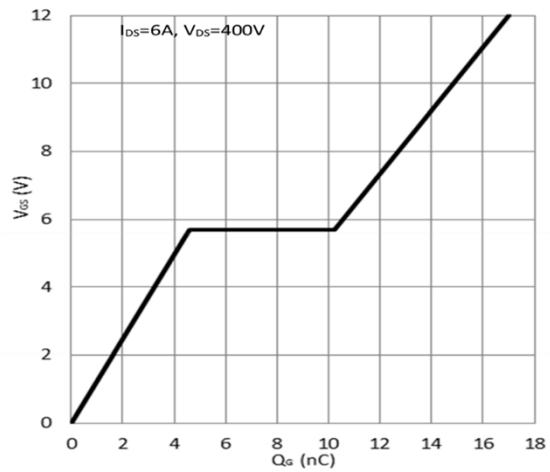


Figure 10. Typical Gate Charge

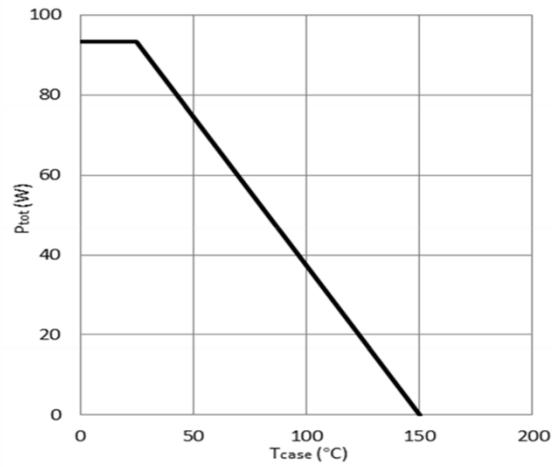


Figure 11. Power Dissipation

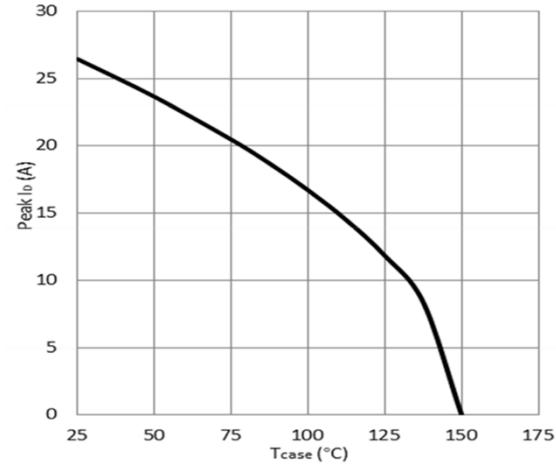


Figure 12. Current Derating

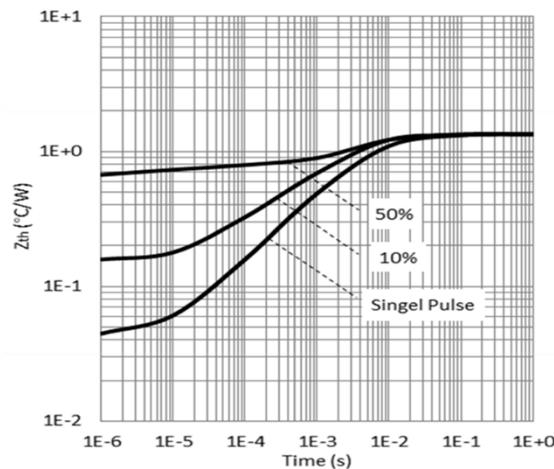


Figure 13. Transient Thermal Resistance

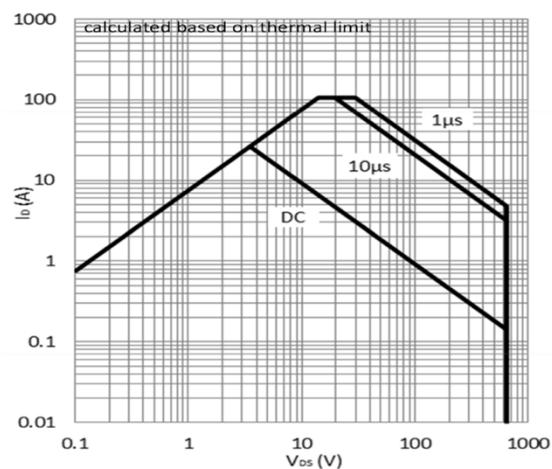


Figure 14. Safe Operating Area  $T_c=25^\circ\text{C}$

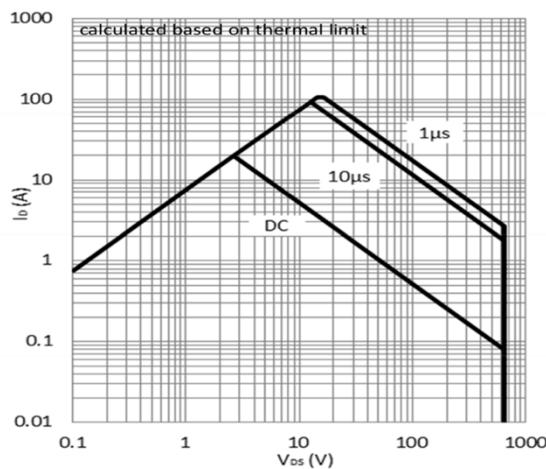


Figure 15. Safe Operating Area  $T_c=80^\circ\text{C}$

## Test Circuits and Waveforms

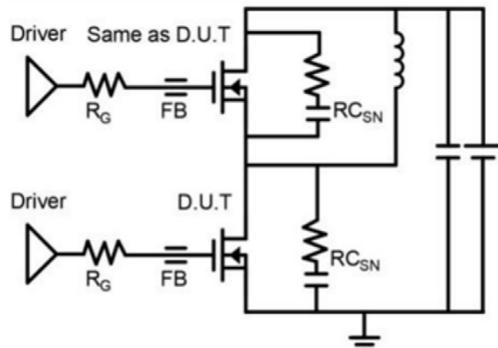


Figure 16. Switching Time Test Circuit

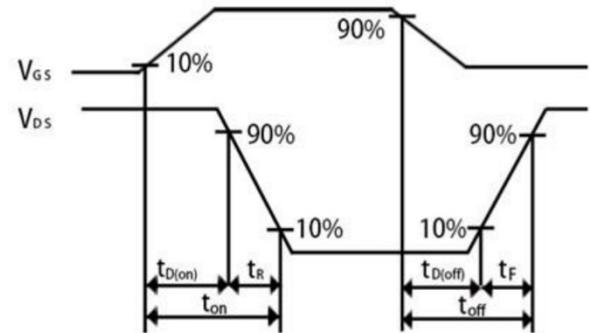


Figure 17. Switching Time Waveform

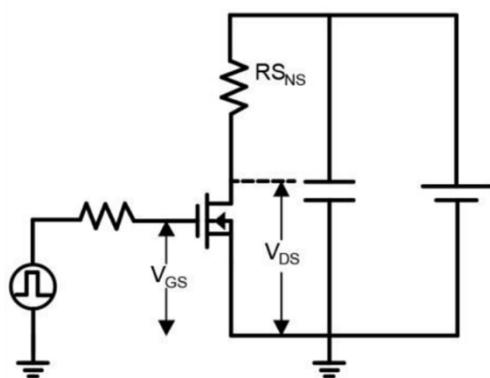
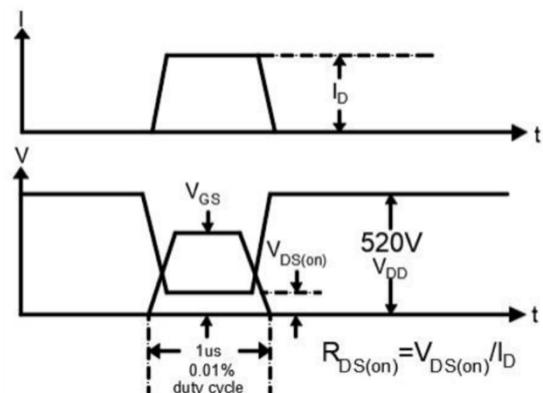
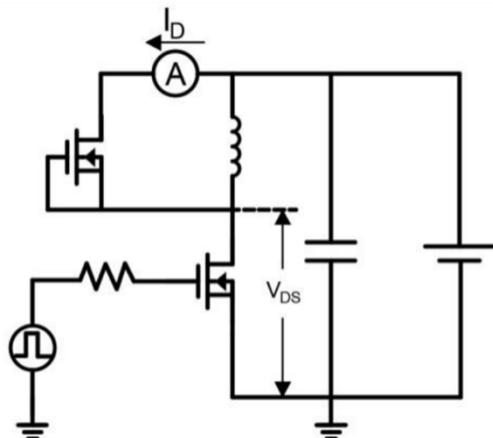
Figure 18. Dynamic  $R_{DS(on)}$  Test CircuitFigure 19. Dynamic  $R_{DS(on)}$  Waveform

Figure 20. Diode Characteristic Test Circuits

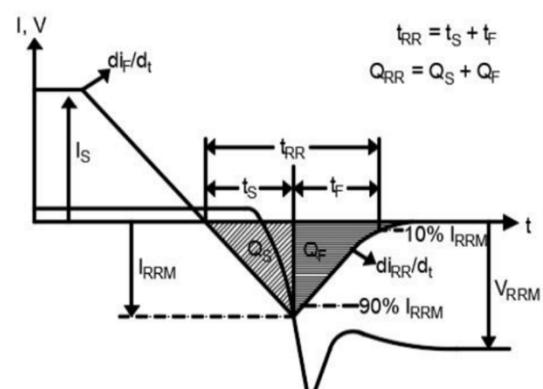
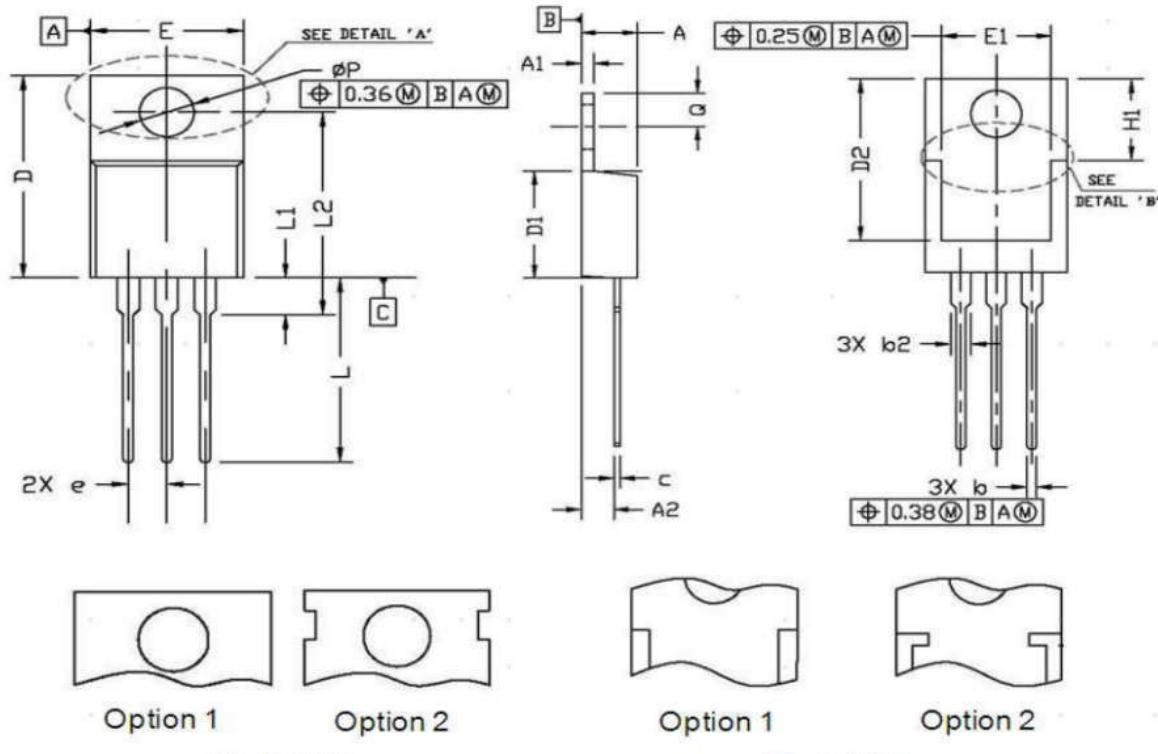


Figure 21. Diode Recovery Waveform

## Product Dimension (TO-220-3L)



SYMBOL	Millimeter		
	Min	Nom	Max
A	4.30	4.50	4.80
A1	1.20	1.30	1.45
A2	2.20	2.50	2.90
b	0.69	0.85	0.95
b2	1.00	1.30	1.60
c	0.33	0.45	0.65
D	14.70	15.50	16.20
D1	8.59	9.00	9.65
D2	11.75	12.70	13.60
e	2.54BSC		
E	9.60	10.00	10.60
E1	7.00	7.50	8.46
H1	6.20	6.60	7.00
L	12.60	13.70	14.80
L1	2.70	3.40	3.80
L2	12.13	14.20	16.50
Q	2.40	2.80	3.10
P	3.50	3.70	3.90

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